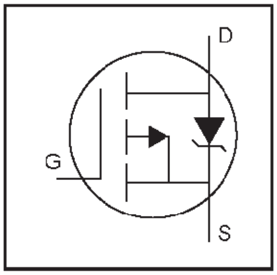
International
IOR Rectifier

PD - 95957

IRF5305S/LPbF

HEXFET® Power MOSFET

- Lead-Free
- Advanced Process Technology
- Surface Mount (IRF5305S)
- Low-profile through-hole (IRF5305L)
- 175°C Operating Temperature
- Fast Switching
- P-Channel
- Fully Avalanche Rated



V_{DSS} = -55V

$R_{DS(on)}$ = 0.06Ω

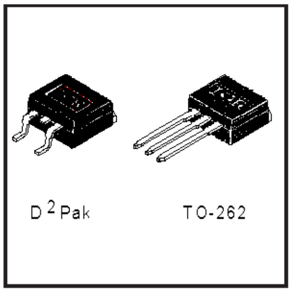
I_D = -31A

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D²Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.

The through-hole version (IRF5305L) is available for low-profile applications.



Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ -10V⑤	-31	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ -10V⑤	-22	
I_{DM}	Pulsed Drain Current ①⑤	-110	
P_D @T_A = 25°C	Power Dissipation	3.8	W
P_D @T_C = 25°C	Power Dissipation	110	W
	Linear Derating Factor	0.71	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy②⑤	280	mJ
I_{AR}	Avalanche Current①	-16	A
E_{AR}	Repetitive Avalanche Energy①	11	mJ
dv/dt	Peak Diode Recovery dv/dt ③⑤	-5.8	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

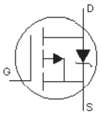
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	–––	1.4	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mounted,steady-state)**	–––	40	

4/21/05

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-55	–––	–––	V	V_{GS} = 0V, I_D = -250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	–––	-0.034	–––	V/°C	Reference to 25°C, I_D = -1mA⑤
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	–––	–––	0.06	Ω	V_{GS} = -10V, I_D = -16A ④
$V_{GS(th)}$	Gate Threshold Voltage	-2.0	–––	-4.0	V	V_{DS} = V_{GS}, I_D = -250μA
g_{fs}	Forward Transconductance	8.0	–––	–––	S	V_{DS} = -25V, I_D = -16A⑤
I_{DSS}	Drain-to-Source Leakage Current	–––	–––	-25	μA	V_{DS} = -55V, V_{GS} = 0V
		–––	–––	-250		V_{DS} = -44V, V_{GS} = 0V, T_J = 150°C
I_{GSS}	Gate-to-Source Forward Leakage	–––	–––	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	–––	–––	-100		V_{GS} = -20V
Q_g	Total Gate Charge	–––	–––	63	nC	I_D = -16A
Q_{gs}	Gate-to-Source Charge	–––	–––	13		V_{DS} = -44V
Q_{gd}	Gate-to-Drain ("Miller") Charge	–––	–––	29		V_{GS} = -10V, See Fig. 6 and 13 ④⑤
$t_{d(on)}$	Turn-On Delay Time	–––	14	–––	ns	V_{DD} = -28V
t_r	Rise Time	–––	66	–––		I_D = -16A
$t_{d(off)}$	Turn-Off Delay Time	–––	39	–––		R_G = 6.8Ω
t_f	Fall Time	–––	63	–––		R_D = 1.6Ω, See Fig. 10 ④⑤
L_S	Internal Source Inductance	–––	7.5	–––	nH	Between lead, and center of die contact
C_{iss}	Input Capacitance	–––	1200	–––	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	–––	520	–––		V_{DS} = -25V
C_{rss}	Reverse Transfer Capacitance	–––	250	–––		ƒ = 1.0MHz, See Fig. 5⑤

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	–––	–––	-31	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	–––	–––	-110		
V_{SD}	Diode Forward Voltage	–––	–––	-1.3	V	T_J = 25°C, I_S = -16A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	–––	71	110	ns	T_J = 25°C, I_F = -16A
Q_{rr}	Reverse Recovery Charge	–––	170	250	nC	di/dt = -100A/μs ④⑤
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② V_{DD} = -25V, Starting T_J = 25°C, L = 2.1mH R_G = 25Ω, I_{AS} = -16A. (See Figure 12)

③ $I_{SD} \leq$ -16A, di/dt ≤ -280A/μs, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq$ 175°C

④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

⑤ Uses IRF5305 data and test conditions

** When mounted on 1" square PCB (FR-4 or G-10 Material).
For recommended footprint and soldering techniques refer to application note #AN-994.

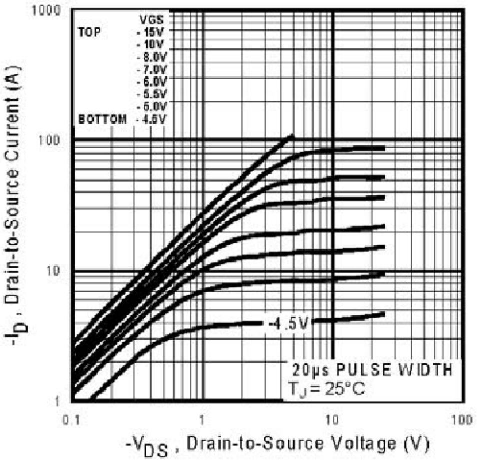


Fig 1. Typical Output Characteristics

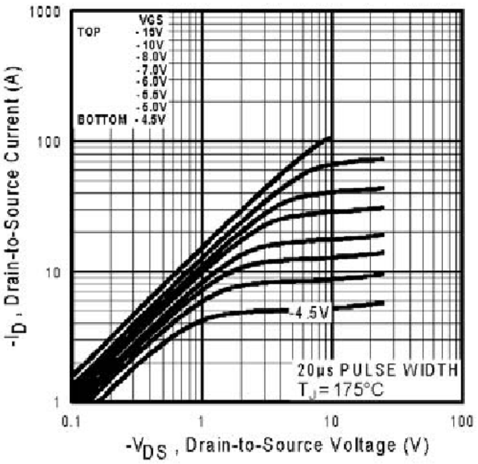


Fig 2. Typical Output Characteristics

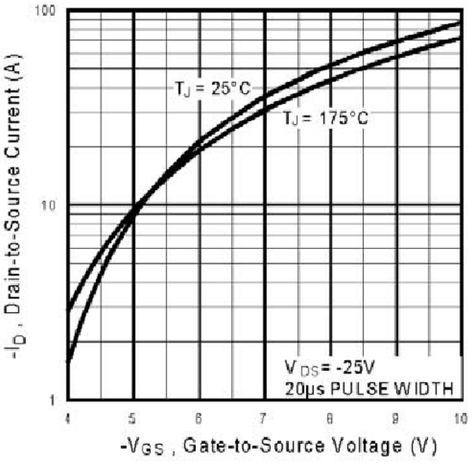


Fig 3. Typical Transfer Characteristics

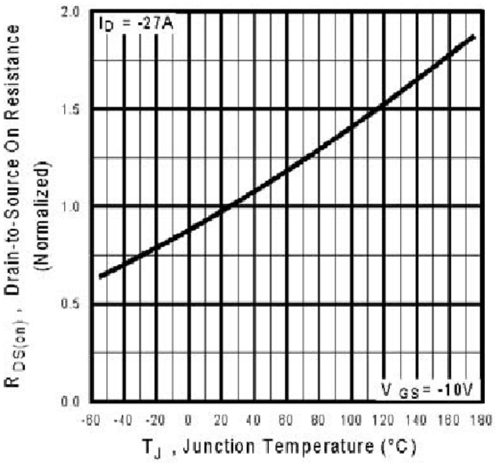


Fig 4. Normalized On-Resistance Vs. Temperature

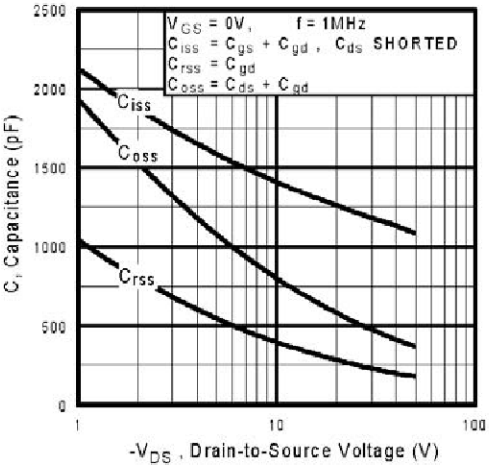


Fig 5. Typical Capacitance Vs.
Drain-to-Source Voltage

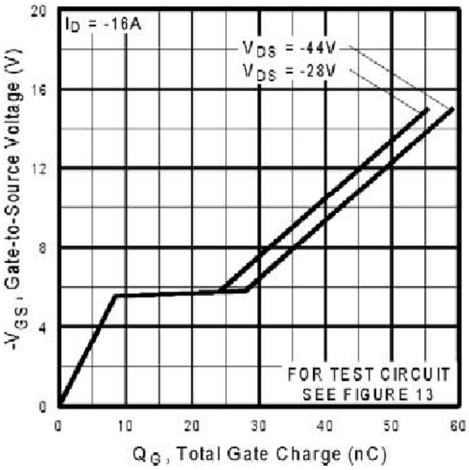


Fig 6. Typical Gate Charge Vs.
Gate-to-Source Voltage

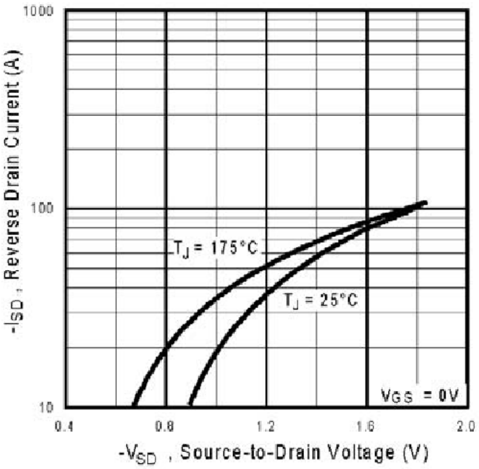


Fig 7. Typical Source-Drain Diode
Forward Voltage

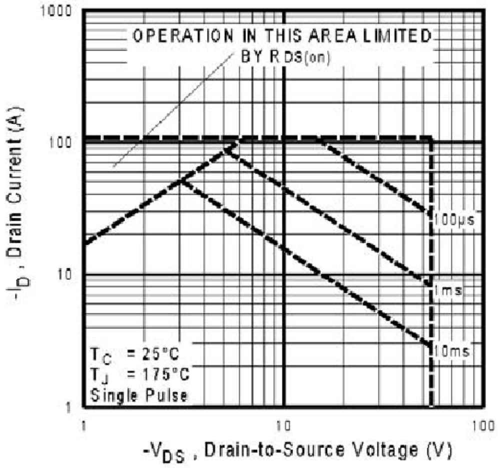


Fig 8. Maximum Safe Operating Area

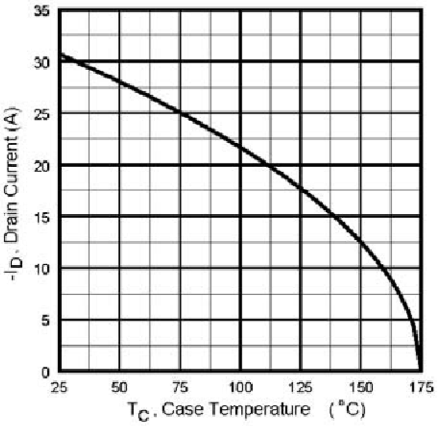


Fig 9. Maximum Drain Current Vs. Case Temperature

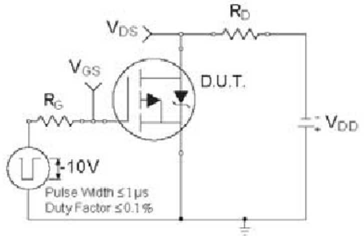


Fig 10a. Switching Time Test Circuit

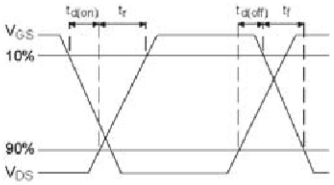


Fig 10b. Switching Time Waveforms

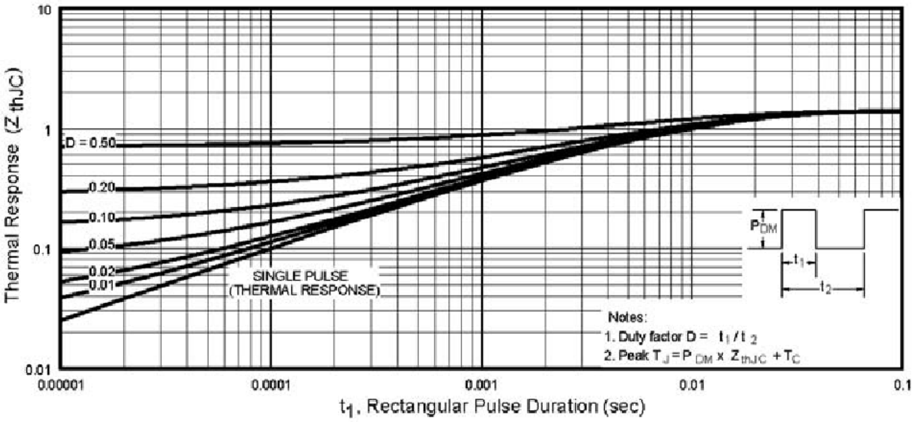


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

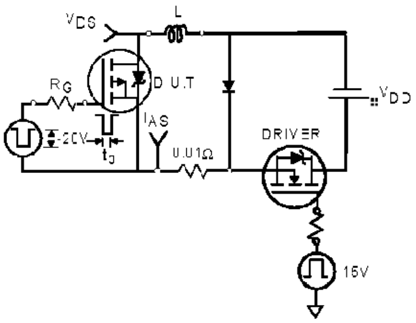


Fig 12a. Unclamped Inductive Test Circuit

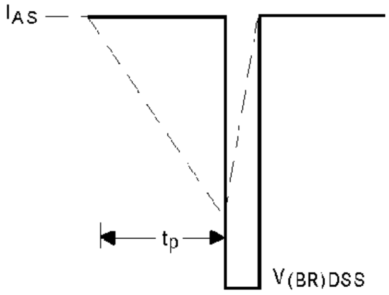


Fig 12b. Unclamped Inductive Waveforms

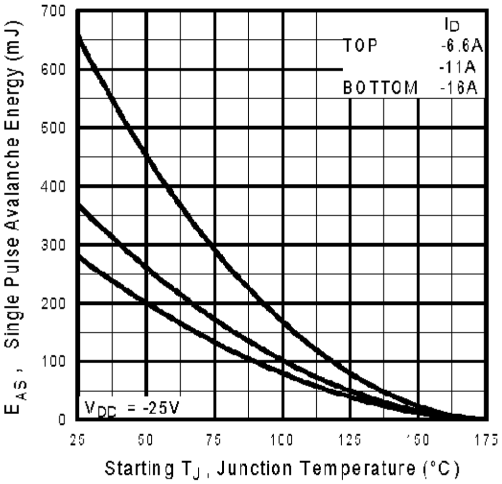


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

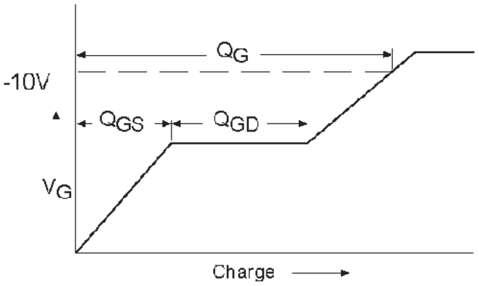


Fig 13a. Basic Gate Charge Waveform

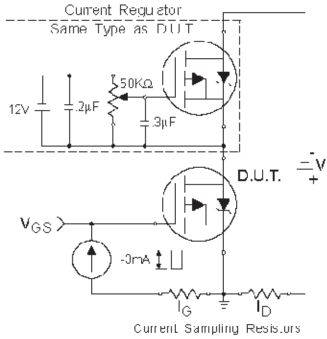
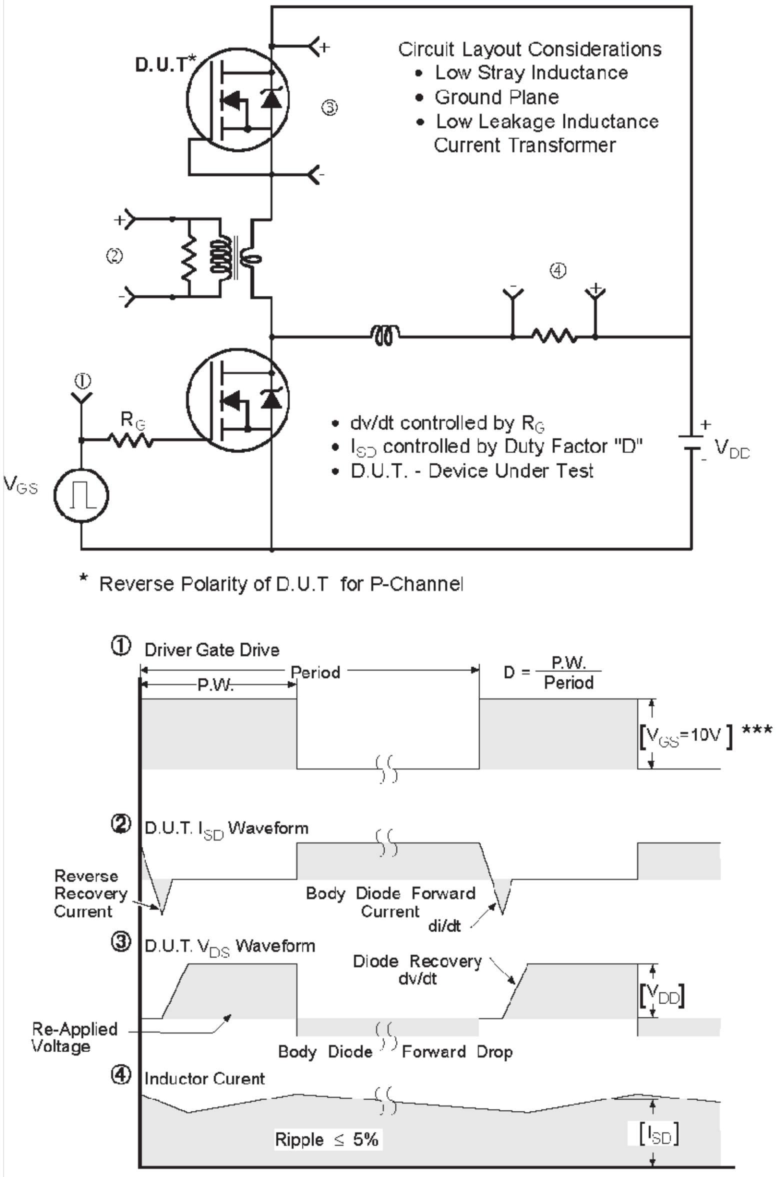


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit

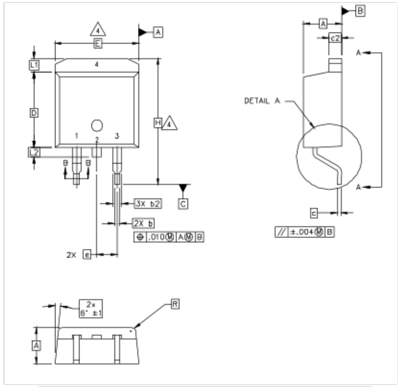


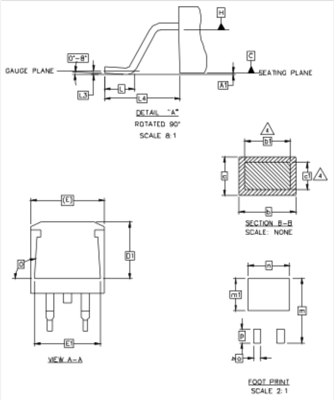
* Reverse Polarity of D.U.T for P-Channel

*** V_{GS} = 5.0V for Logic Level and 3V Drive Devices

Fig 14. For P-Channel HEXFETS

D^{2}Pak Package Outline





NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	0.00	0.254	.000	.010	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.78	.045	.070	
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	4
c2	1.14	1.65	.045	.065	
D	8.51	9.65	.335	.380	3
D1	6.86		.270		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
H	14.61	15.88	.575	.625	
L	1.78	2.79	.070	.110	
L1		1.65		.065	
L2	1.27	1.78	.050	.070	
L3	0.25 BSC		.010 BSC		
L4	4.78	5.28	.188	.208	
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
R	0.51	0.71	.020	.028	
θ	90°	93°	90°	93°	

LEAD ASSIGNMENTS

HEXFET

1.- GATE
2, 4.- DRAIN
3.- SOURCE

IGBTs, CoPACK

1.- GATE
2, 4.- COLLECTOR
3.- EMITTER

DIODES

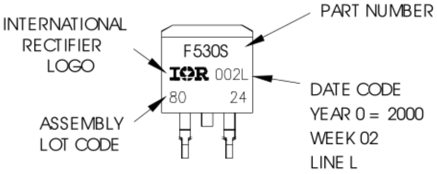
1.- ANODE *
2, 4.- CATHODE
3.- ANODE

* PART DEPENDENT.

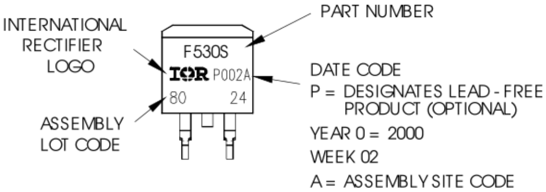
D^{2}Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW 02, 2000
IN THE ASSEMBLY LINE "L"

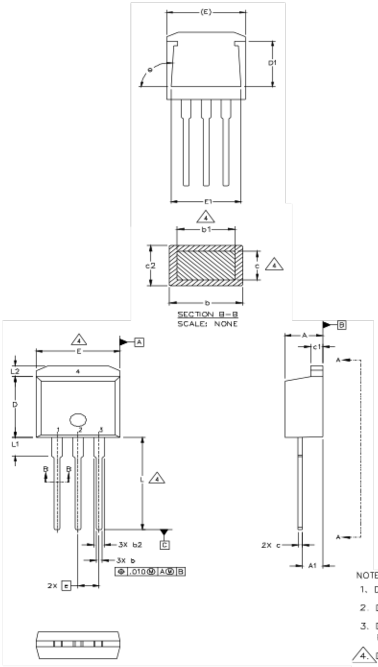
Note: "P" in assembly line position indicates "Lead - Free"



OR



TO-262 Package Outline



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	2.03	2.92	.080	.115	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.40	.045	.055	
c	0.38	0.63	.015	.025	4
c1	1.14	1.40	.045	.055	
c2	0.43	.063	.017	.029	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	13.46	14.09	.530	.555	
L1	3.56	3.71	.140	.146	
L2		1.65		.065	

LEAD ASSIGNMENTS

HEXFET

1.— GATE
2.— DRAIN
3.— SOURCE
4.— DRAIN

IGBT

1 - GATE
2 - COLLECTOR
3 - EMITTER

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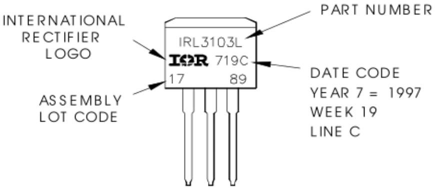
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

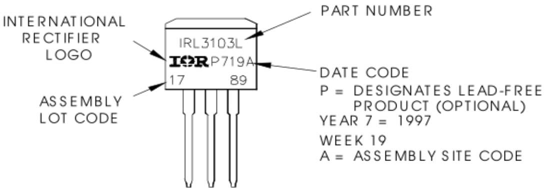
TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead-Free"

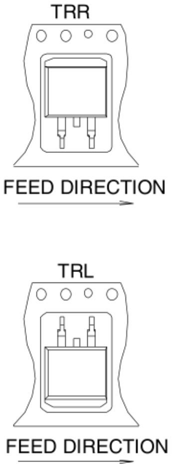


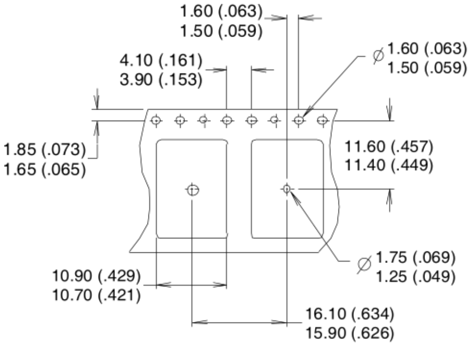
OR

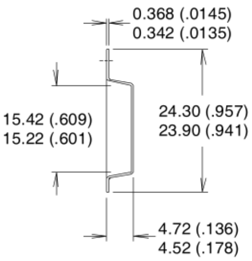


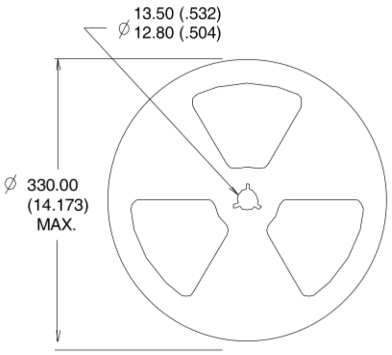
D²Pak Tape & Reel Information

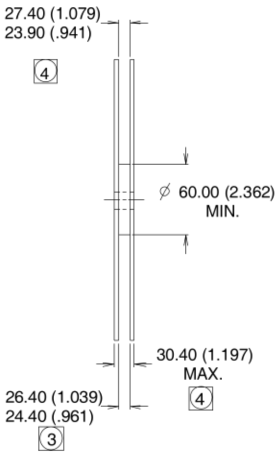
Dimensions are shown in millimeters (inches)











NOTES :

1. COMFORMS TO EIA-418.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION MEASURED @ HUB.
4. INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Data and specifications subject to change without notice.

International
IOR Rectifier

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TAC Fax: (310) 252-7903
Visit us at www.irf.com for sales contact information.04/05

Note: For the most current drawings please refer to the IR website at:
http://www.irf.com/package/